

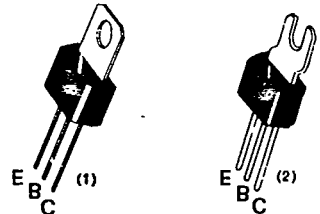
PNP SILICON ANNULAR* TRANSISTORS

... designed for complementary symmetry audio circuits

- Excellent Current Gain Linearity — 1.0 mAdc to 1.0 Adc
- Low Collector-Emitter Saturation Voltage —
 $V_{CE(sat)} = 0.7 \text{ Vdc (Max) @ } I_C = 1.0 \text{ Adc}$
- Complements to NPN BD505, BD507, BD509
- Uniwatt^A Package for Excellent Thermal Properties —
 1.0 Watt @ $T_A = 25^\circ\text{C}$
 10.0 Watts @ $T_C = 25^\circ\text{C}$

PNP SILICON
AUDIO TRANSISTORS

20 - 30 - 40 VOLTS
 10 WATTS



(1) Standard package: BD506, 508, 510
 (2) Tab formed for flat mounting BD506-1, 508-1, 510-1

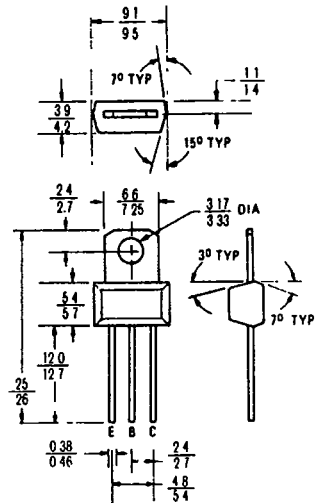
Also available with leads formed to TO-5 configuration: BD506-5, 508-5, 510-5

MAXIMUM RATINGS

Rating	Symbol	BD506	BD508	BD510	Unit
Collector-Emitter Voltage	V_{CEO}	20	30	40	Vdc
Collector-Base Voltage	V_{CB}	30	40	50	Vdc
Emitter-Base Voltage	V_{EB}	5.0			Vdc
Collector Current - Continuous	I_C	2.0			Adc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.0			Watt
		8.0			mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	10			Watts
		80			mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150			$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	125	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient	θ_{JA}	125	$^\circ\text{C/W}$



All dimensions in millimeters
 Collector connected
 to tab

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage ($I_C = 1.0 \text{ mAdc}$, $I_B = 0$)	BD506 BD508 BD510 BV_{CEO}	20 30 40	— — —	— — —	Vdc
Emitter-Base Breakdown Voltage ($I_E = 100 \mu\text{Adc}$, $I_C = 0$)	BV_{EBO}	5.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 20, 30, 40 \text{ Vdc}$, $I_E = 0$)	BD506 BD508 BD510 I_{CBO}	— — —	— — —	100 100 100	nAdc

ON CHARACTERISTICS

DC Current Gain (1) ($I_C = 250 \text{ mAdc}$, $V_{CE} = 2.0 \text{ Vdc}$) ($I_C = 1.0 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$)	h_{FE}	60 40	135 90	— —	—
Collector-Emitter Saturation Voltage (1) ($I_C = 1.0 \text{ Adc}$, $I_B = 0.1 \text{ Adc}$)	$V_{CE(sat)}$	—	0.40	0.7	Vdc
Base-Emitter On Voltage (1) ($I_C = 1.0 \text{ Adc}$, $V_{CE} = 1.0 \text{ Vdc}$)	$V_{BE(on)}$	—	0.92	1.2	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain-Bandwidth Product ($I_C = 50 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f_T	50	180	—	MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f = 100 \text{ kHz}$)	C_{ob}	—	—	30	pF

(1) Pulse Test Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 20\%$

FIGURE 1 — DC CURRENT GAIN

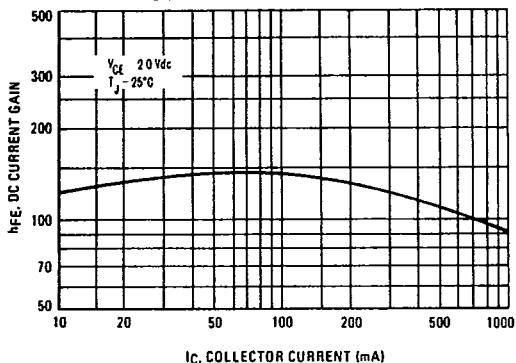


FIGURE 2 — "ON" VOLTAGES

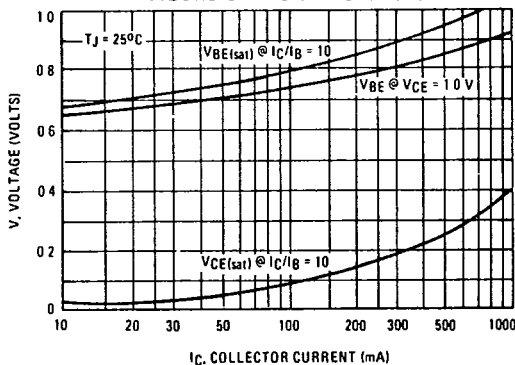
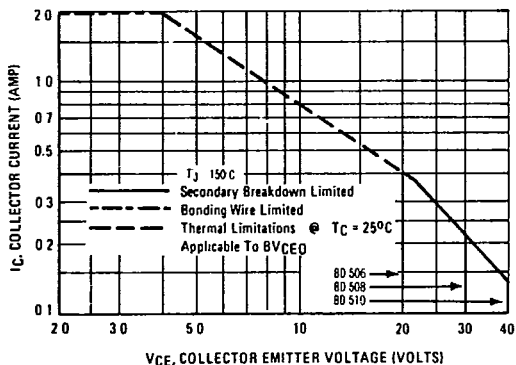


FIGURE 3 — DC SAFE OPERATING AREA



There are two limitations on the power handling ability of a transistor: junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 3 is based on $T_J(pk) = 150^\circ\text{C}$; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by secondary breakdown.